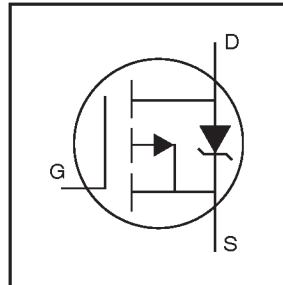


# IRF5305PbF

HEXFET® Power MOSFET

- Advanced Process Technology
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- P-Channel
- Fully Avalanche Rated
- Lead-Free

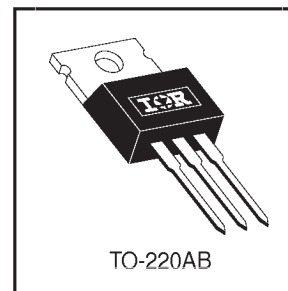


$V_{DSS} = -55V$
$R_{DS(on)} = 0.06\Omega$
$I_D = -31A$

## Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The TO-220 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 watts. The low thermal resistance and low package cost of the TO-220 contribute to its wide acceptance throughout the industry.



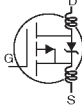
## Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V$	-31	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ -10V$	-22	
$I_{DM}$	Pulsed Drain Current ①	-110	
$P_D @ T_C = 25^\circ C$	Power Dissipation	110	W
	Linear Derating Factor	0.71	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$E_{AS}$	Single Pulse Avalanche Energy ②	280	mJ
$I_{AR}$	Avalanche Current ③	-16	A
$E_{AR}$	Repetitive Avalanche Energy ①	11	mJ
dv/dt	Peak Diode Recovery dv/dt ③	-5.0	V/ns
$T_J$	Operating Junction and	-55 to + 175	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds		
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

## Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	1.4	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient	—	62	

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-55	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	-0.034	—	V/°C	Reference to $25^\circ\text{C}$ , $I_D = -1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.06	$\Omega$	$V_{GS} = -10V, I_D = -16A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	-2.0	—	-4.0	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
$g_{fs}$	Forward Transconductance	8.0	—	—	S	$V_{DS} = -25V, I_D = -16A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	-25	$\mu A$	$V_{DS} = -55V, V_{GS} = 0V$
		—	—	-250		$V_{DS} = -44V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
$Q_g$	Total Gate Charge	—	—	63	nC	$I_D = -16A$
$Q_{gs}$	Gate-to-Source Charge	—	—	13		$V_{DS} = -44V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	—	29		$V_{GS} = -10V$ , See Fig. 6 and 13 ④
$t_{d(on)}$	Turn-On Delay Time	—	14	—	ns	$V_{DD} = -28V$
$t_r$	Rise Time	—	66	—		$I_D = -16A$
$t_{d(off)}$	Turn-Off Delay Time	—	39	—		$R_G = 6.8\Omega$
$t_f$	Fall Time	—	63	—		$R_D = 1.6\Omega$ , See Fig. 10 ④
$L_D$	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
$L_S$	Internal Source Inductance	—	7.5	—		
$C_{iss}$	Input Capacitance	—	1200	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	520	—		$V_{DS} = -25V$
$C_{rss}$	Reverse Transfer Capacitance	—	250	—		$f = 1.0\text{MHz}$ , See Fig. 5

## Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	-31	A	MOSFET symbol showing the integral reverse p-n junction diode.
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	-110		
$V_{SD}$	Diode Forward Voltage	—	—	-1.3	V	$T_J = 25^\circ\text{C}, I_S = -16A, V_{GS} = 0V$ ④
$t_{rr}$	Reverse Recovery Time	—	71	110	ns	$T_J = 25^\circ\text{C}, I_F = -16A$
$Q_{rr}$	Reverse Recovery Charge	—	170	250	nC	$di/dt = -100A/\mu s$ ④

### Notes:

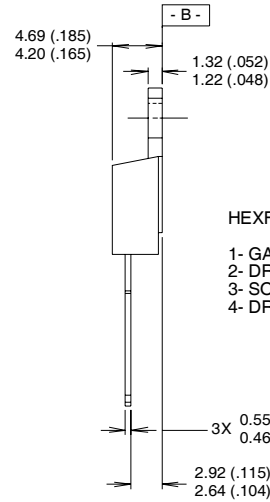
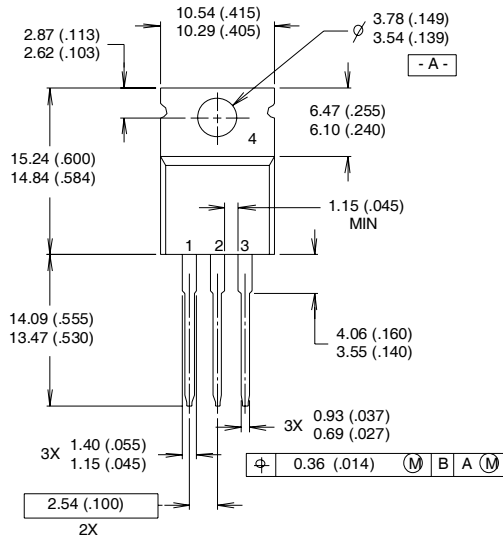
- ① Repetitive rating; pulse width limited by max. junction temperature. ( See fig. 11 )
- ②  $V_{DD} = -25V$ , starting  $T_J = 25^\circ\text{C}$ ,  $L = 2.1\text{mH}$   
 $R_G = 25\Omega, I_{AS} = -16A$ . (See Figure 12)
- ③  $I_{SD} \leq -16A, di/dt \leq -280A/\mu s, V_{DD} \leq V_{(BR)DSS}, T_J \leq 175^\circ\text{C}$
- ④ Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$ .

# IRF5305PbF



## TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



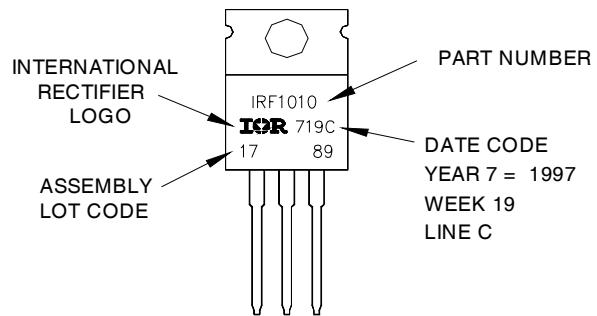
LEAD ASSIGNMENTS	
HEXFET	IGBTs, CoPACK
1- GATE	1- GATE
2- DRAIN	2- COLLECTOR
3- SOURCE	3- EMITTER
4- DRAIN	4- COLLECTOR

**NOTES:**

- 1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
- 2 CONTROLLING DIMENSION : INCH
- 3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.
- 4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

## TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010  
 LOT CODE 1789  
 ASSEMBLED ON WW 19, 1997  
 IN THE ASSEMBLY LINE "C"  
**Note:** "P" in assembly line position indicates "Lead-Free"



Data and specifications subject to change without notice.

